Supporting information for:

Rutile to Anatase phase transition induced by N doping in highly oriented TiO₂ films

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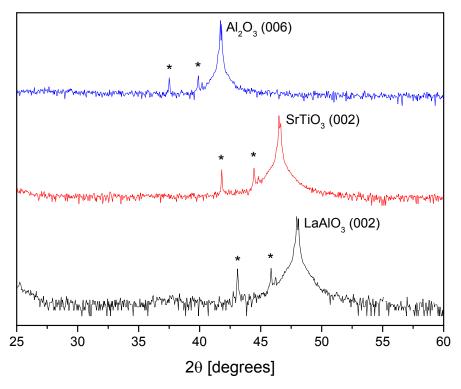


Figure S1. XRD patterns of uncoated substrates

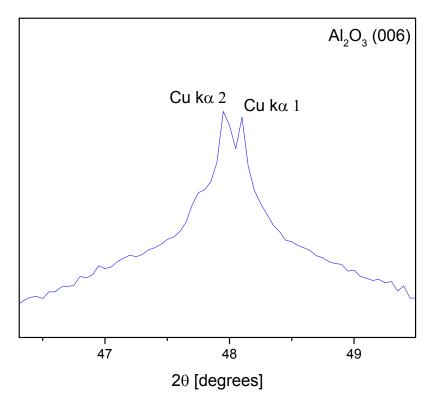


Figure S2. XRD of Al_2O_3 (006) showing splitting due to $k\alpha_1$ and $k\alpha_2$ wavelengths

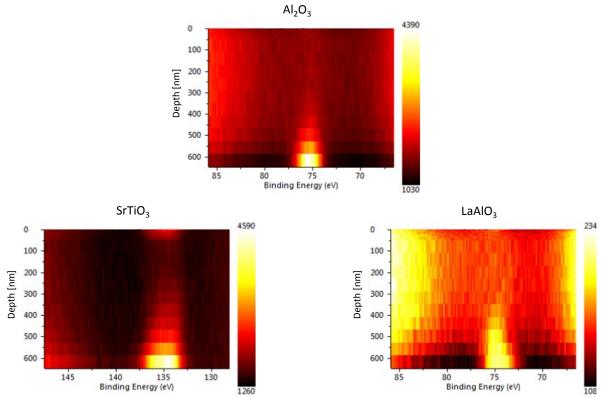


Figure S3. XPS depth profiles of TiO_2 films on AI_2O_3 , $SrTiO_3$, and $LaAIO_3$ displayed as a heat map. For films grown on AI_2O_3 the Al 2p region is shown, for $SrTiO_3$ the Sr 3d region is shown, and for $LaAIO_3$ the Al 2p region is shown. These regions are used to identify the depth of the filmsubstrate interface and hence the thickness of the films.

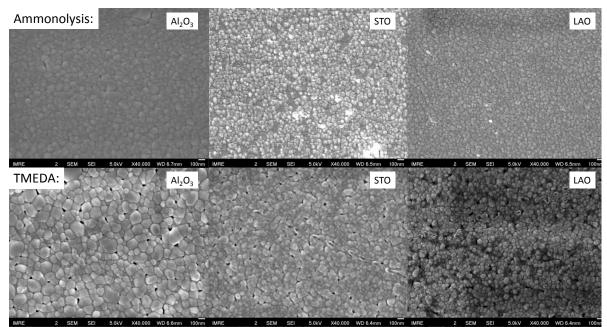


Figure S4. SEM images of nitrogen doped TiO₂ films (ammonolysis top, TMEDA bottom)